

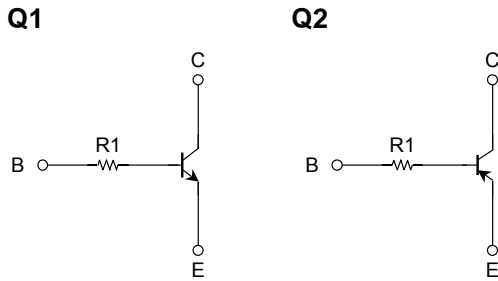
TOSHIBA Transistor Silicon NPN·PNP Epitaxial Type
(PCT process) (Bias Resistor Built-in Transistor)

RN4990FS

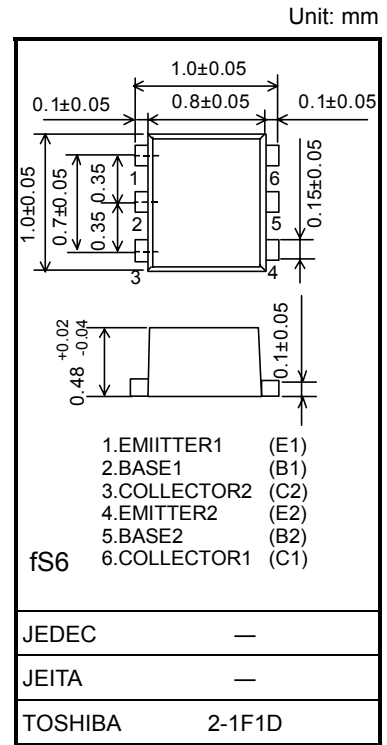
Switching, Inverter Circuit, Interface Circuit and
Driver Circuit Applications

- Two devices are incorporated into a fine pitch small mold (6-pin) package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enables the manufacture of ever more compact equipment and lowers assembly cost.

Equivalent Circuit and Bias Resistor Values

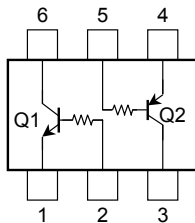


R1: 4.7kΩ
(Q1, Q2 common)

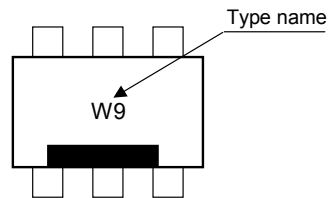


Weight: 0.001g (typ.)

Equivalent Circuit (top view)



Marking



Maximum Ratings (Ta = 25°C) (Q1)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA

Maximum Ratings (Ta = 25°C) (Q2)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-50	mA

Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Rating	Unit
Collector power dissipation	P_C (Note)	50	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C

Note: Total rating

Electrical Characteristics (Ta = 25°C) (Q1)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 20\text{ V}, I_E = 0$	—	—	100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	100	nA
DC current gain	h_{FE}	$V_{CE} = 5\text{ V}, I_C = 1\text{ mA}$	300	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 5\text{ mA}, I_B = 0.25\text{ mA}$	—	—	0.15	V
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	1.2	—	pF

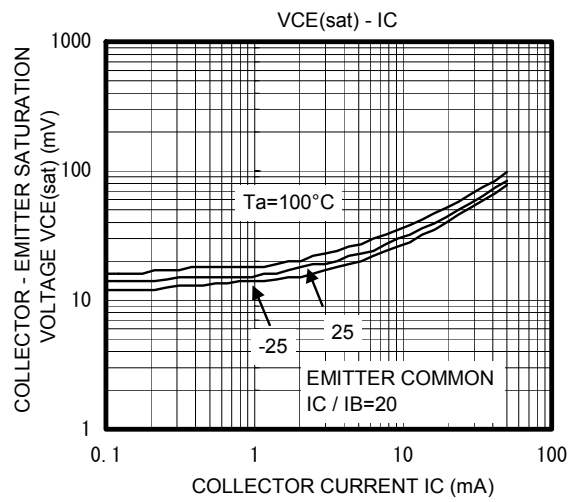
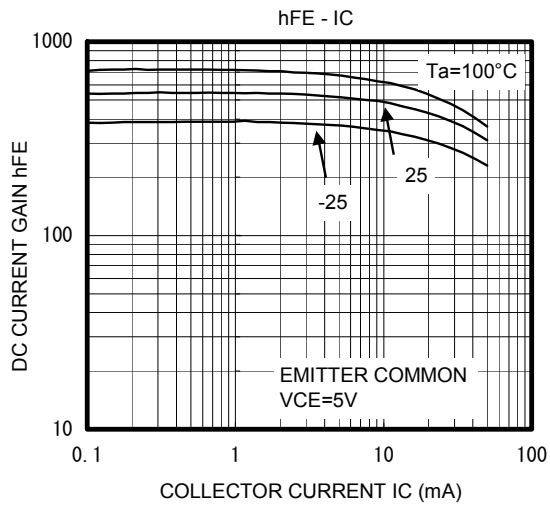
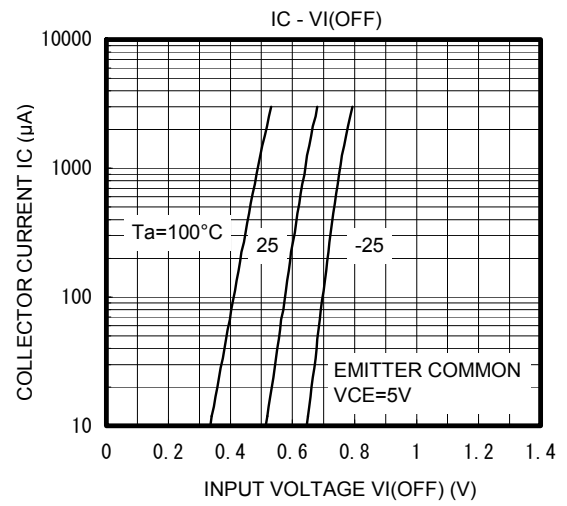
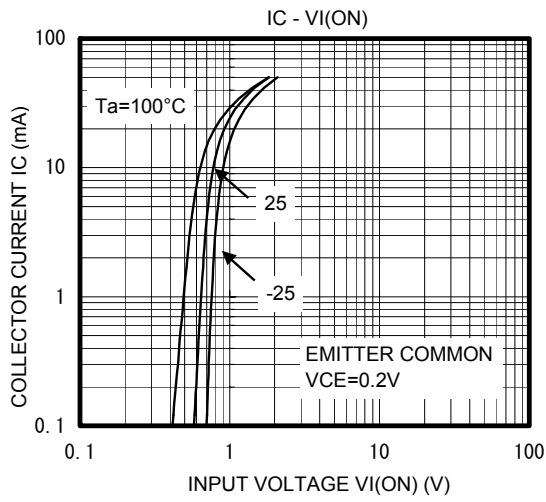
Electrical Characteristics (Ta = 25°C) (Q2)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -20\text{ V}, I_E = 0$	—	—	-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-100	nA
DC current gain	h_{FE}	$V_{CE} = -5\text{ V}, I_C = -1\text{ mA}$	300	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	—	-0.15	V
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	1.2	—	pF

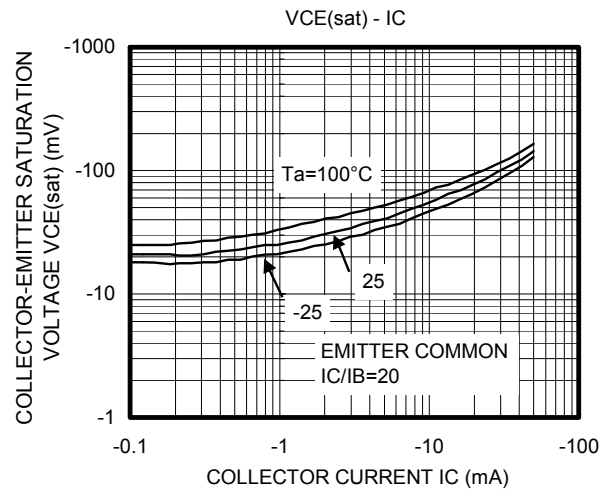
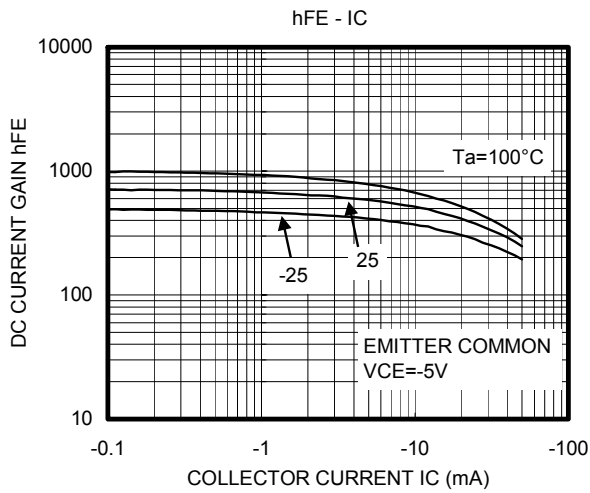
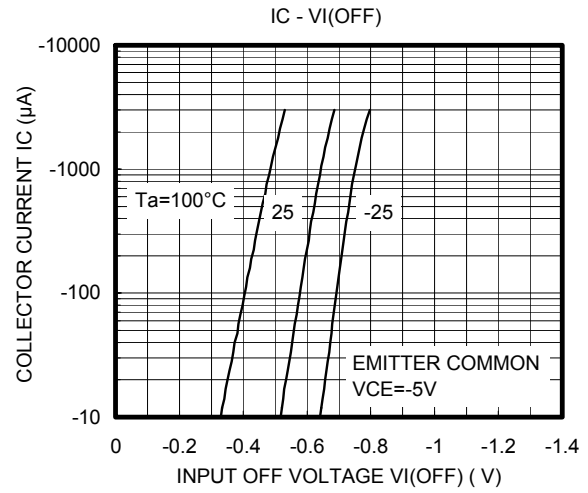
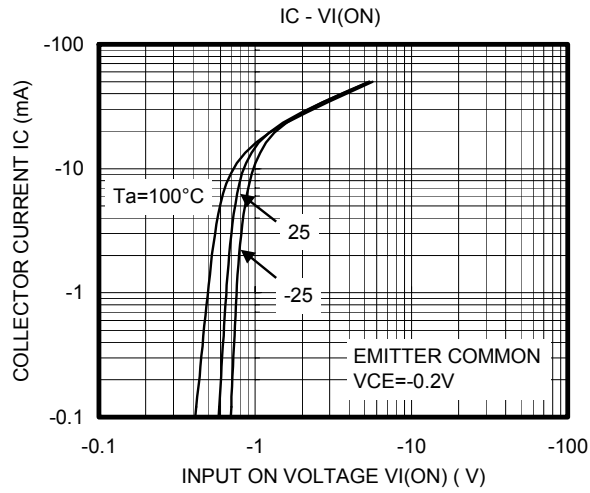
Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input resistor	R1	—	3.76	4.7	5.64	kΩ

Q1



Q2



HANDLING PRECAUTION

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic discharge. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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